

WHAT IS CLAIMED IS:

1. A semiconductor device comprising:

n (n is an integer equal to or greater than 2) thin film  
5 transistors provided between an element to be driven which operates  
based on supplied power and a power supply line for supplying power  
to said element to be driven, for controlling power supplied to  
said element to be driven; wherein

the number of contact points for electrically connecting said  
10 n thin film transistors and corresponding element to be driven is  
equal to or less than (n-1).

2. A semiconductor device according to claim 1, wherein

said n thin film transistors and corresponding element to be  
15 driven are electrically connected to each other by a wiring layer;  
and

the contact position between the wiring layer and the thin  
film transistor is placed to be distant from the contact position  
between the wiring layer and said element to be driven.

3. A semiconductor device according to claim 2, wherein

said element to be driven is an emissive element which  
includes an emissive element layer between a first electrode and  
a second electrode;

25 a contact hole is formed on an insulation layer which is formed  
above said wiring layer, said wiring layer being connected through  
the contact hole to said first electrode of said emissive element  
which is formed on top of said insulation layer and covering said  
contact hole;

at least the contact hole region of said first electrode is covered by a flattening layer; and

said emissive element layer is formed above said first electrode and said flattening layer.

5

4. A semiconductor device according to claim 1, wherein

said n thin film transistors and corresponding element to be driven are directly or indirectly and electrically connected to each other at a contact hole formed on an insulation layer for separating said thin film transistor which is formed at a lower layer and said element to be driven;

10

at least the contact hole region of said first electrode is covered by a flattening layer; and

an emissive element layer is formed above said first electrode and said flattening layer.

15

5. A semiconductor device according to claim 1, wherein said element to be driven is an organic electroluminescence element which uses an organic compound in an emissive layer.

20